



MMDT3906\

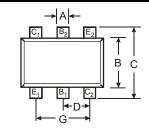
DUAL PNP SMALL SIGNAL SURFACE MOUNT TRANSISTOR

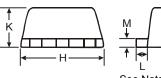
Features

- **Epitaxial Planar Die Construction**
- Ideal for Low Power Amplification and Switching
- Ultra-Small Surface Mount Package
- Lead Free By Design/RoHS Compliant (Note 1)
- Qualified to AEC-Q101 Standards for High Reliability
- "Green" Device (Note 4 and 5)

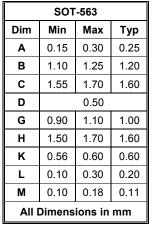
Mechanical Data

- Case: SOT-563
- Case Material: Molded Plastic. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020C
- Terminal Connections: See Diagram
- Terminals: Finish Matte Tin annealed over Alloy 42 leadframe. Solderable per MIL-STD-202, Method 20
- Terminals: Lead bearing terminal plating available. See Ordering information Page 3
- Marking & Type Code Information:
- Ordering Information: See Page 3
- Weight: 0.003 grams (approximate)









See Page 3		<u> </u>	T]	_	ナ ヿ
	E ₁		B ₁		C ₂

Maximum Ratings @TA = 25°C unless otherwise specified

Characteristic	Symbol	Value	Unit	
Collector-Base Voltage	V _{CBO}	-40	V	
Collector-Emitter Voltage	V _{CEO}	-40	V	
Emitter-Base Voltage	V _{EBO}	-5.0	V	
Collector Current - Continuous	Ic	-200	mA	

Thermal Characteristics

Characteristic		Symbol	Value	Unit
Power Dissipation	(Note 3) @ T _A = 25°C	P_d	150	mW
Thermal Resistance, Junction to Ambient	(Note 3) @ T _A = 25°C	$R_{ heta JA}$	833	°C/W
Operating and Storage Temperature Range		T _j , T _{STG}	-55 to +150	°C

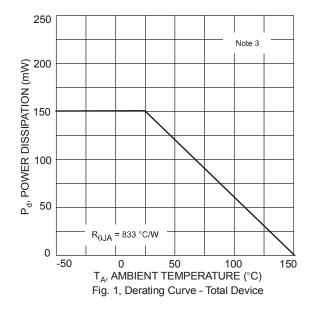
- 1. No purposefully added lead.
- 2. Package is non-polarized. Parts may be on reel in orientation illustrated, 180° rotated, or mixed (both ways).
- 3. Device mounted on FR-4 PCB, 1 inch x 0.85 inch x 0.062 inch; pad layout as shown on Diodes Inc. suggested pad layout document AP02001, which can be found on our website at http://www.diodes.com/datasheets/ap02001.pdf.
- Diodes Inc.'s "Green" policy can be found on our website at http://www.diodes.com/products/lead_free/index.php.
- Product manufactured with Date Code UO (week 40, 2007) and newer are built with Green Molding Compound. Product manufactured prior to Date Code UO are built with Non-Green Molding Compound and may contain Halogens or Sb2O3 Fire Retardants.

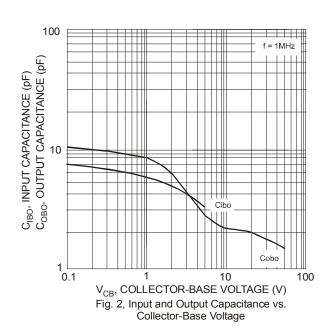


Electrical Characteristics @TA = 25°C unless otherwise specified

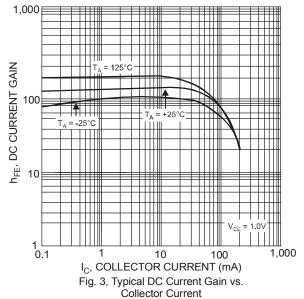
Characteristic	Symbol Min		Max	Unit	Test Condition		
OFF CHARACTERISTICS (Note 6)				•			
Collector-Base Breakdown Voltage	V _{(BR)CBO}	-40		V	$I_C = -10\mu A, I_E = 0$		
Collector-Emitter Breakdown Voltage	V _{(BR)CEO}	-40		V	$I_C = -1.0 \text{mA}, I_B = 0$		
Emitter-Base Breakdown Voltage	V _{(BR)EBO}	-5.0		V	$I_E = -10\mu A$, $I_C = 0$		
Collector Cutoff Current	I _{CEX}		-50	nA	$V_{CE} = -30V, V_{EB(OFF)} = -3.0V$		
Base Cutoff Current	I _{BL}		-50	nA	$V_{CE} = -30V, V_{EB(OFF)} = -3.0V$		
ON CHARACTERISTICS (Note 6)							
DC Current Gain	h _{FE}	60 80 100 60 30	 300 	_	$\begin{split} I_{C} &= -100 \mu A, V_{CE} = -1.0 V \\ I_{C} &= -1.0 m A, V_{CE} = -1.0 V \\ I_{C} &= -10 m A, V_{CE} = -1.0 V \\ I_{C} &= -50 m A, V_{CE} = -1.0 V \\ I_{C} &= -100 m A, V_{CE} = -1.0 V \end{split}$		
Collector-Emitter Saturation Voltage	V _{CE(SAT)}		-0.25 -0.40	V	$I_C = -10$ mA, $I_B = -1.0$ mA $I_C = -50$ mA, $I_B = -5.0$ mA		
Base-Emitter Saturation Voltage	V _{BE(SAT)}	-0.65 —	-0.85 -0.95	٧	$I_C = -10$ mA, $I_B = -1.0$ mA $I_C = -50$ mA, $I_B = -5.0$ mA		
SMALL SIGNAL CHARACTERISTICS							
Output Capacitance	C_{obo}		4.5	pF	$V_{CB} = -5.0V$, $f = 1.0MHz$, $I_E = 0$		
Input Capacitance	C _{ibo}	_	10	pF	$V_{EB} = -0.5V$, $f = 1.0MHz$, $I_C = 0$		
Input Impedance	h _{ie}	2.0	12	kΩ			
Voltage Feedback Ratio	h _{re}	0.1	10	x 10 ⁻⁴	V _{CE} = 10V, I _C = 1.0mA,		
Small Signal Current Gain	h _{fe}	100	400		f = 1.0kHz		
Output Admittance	h _{oe}	3.0	60	μS			
Current Gain-Bandwidth Product	f _T	250	_	MHz	$V_{CE} = -20V, I_C = -10mA,$ f = 100MHz		
Noise Figure	NF	_	4.0	dB	V_{CE} = -5.0V, I_{C} = -100 μ A, R_{S} = 1.0k Ω , f = 1.0kHz		
SWITCHING CHARACTERISTICS	•						
Delay Time	t _d		35	ns	V _{CC} = -3.0V, I _C = -10mA,		
Rise Time	t _r		35	ns	$V_{BE(off)} = 0.5V, I_{B1} = -1.0mA$		
Storage Time	ts	_	225	ns	V _{CC} = -3.0V, I _C = -10mA,		
Fall Time	t _f	_	75	ns	I _{B1} = I _{B2} = -1.0mA		

Notes: 6. Short duration pulse test used to minimize self-heating effect.









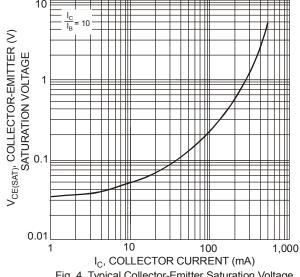
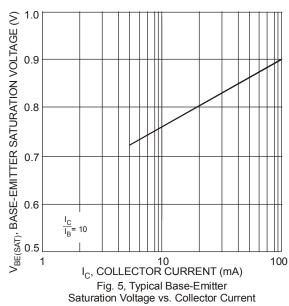


Fig. 4, Typical Collector-Emitter Saturation Voltage vs. Collector Current

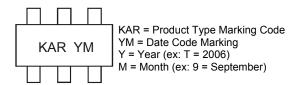


Ordering Information (Note 7)

Device	Packaging	Shipping
MMDT3906V-7	SOT-563	3000/Tape & Reel

Notes: 7. For packaging details, go to our website at http://www.diodes.com/datasheets/ap02007.pdf.

Marking Information



Date Code Key

Year	2005		2006	2007		2008	2009		2010	201	ı	2012
Code	S		Т	U		V	W		Х	Y		Z
Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Au	g Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	0	N	D



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>>Diodes Incorporated(达迩科技(美台))